

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/796,387	HORNG ET AL.	
Examiner		Art Unit		Page 1 of 1
William J. Klimowicz		2627		

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,968,676	10-1999	Araki et al.	428/811
*	B	US-6,270,593	08-2001	Shindo et al.	148/442
*	C	US-6,841,395	01-2005	Linn et al.	438/3
*	D	US-2004/0021990	02-2004	Koui et al.	360/324.1
*	E	US-2004/0206619	10-2004	Pinarbasi, Mustafa	204/192.2
*	F	US-2006/0057745	03-2006	Horng et al.	438/003
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	EP 883196 A2	12-1998	European Patent	ARAKI et al.	
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Fukumoto, "Magneto resistive device manufacturing method for magnetic random access memory, involves exposing lower ferromagnetic layer to gas containing oxygen atoms as set pressure and forming upper ferromagnetic layer having set thickness," Jan. 19, 2006, WIPO 2006006630 A1, 37 pp.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.